

## 6/8inch SiC Etcher

### Model: SA-GDE C200

SA-GDE C200 is a high plasma density etcher designed for 6/8-inch SiC power, MEMS and GaAs RF devices, executing SiC trench, via and mark etching. With dual-coil RF source and 2650L/s turbo pump, it reaches 6000A/min SiC etch rate. Y<sub>2</sub>O<sub>3</sub>-coated components reduce contamination, delivering long MTBC and reliable mass-production performance for wide-bandgap semiconductors.



#### Feature

- Higher Plasma Density
- Comparable
- Higher ER
- More Stable
- Longer duration

#### Application

- BAW
- SiC Power
- VCSEL
- MEMS
- GaN/GaAs RF

#### Specifications:

| Parameter           | Descriptions                            |
|---------------------|-----------------------------------------|
| Wafer Size          | 6/8inch                                 |
| Etching Materials   | SiC/SiO <sub>2</sub> /SiN/Polymer/AlScN |
| Processes           | SiC trench/SiC Via/Sic Mark             |
| Source-RF           | Dual coil,13.56MHz                      |
| Source Range        | 3000W+3000W                             |
| Bias-RF             | 13.56MHz                                |
| Top Window          | Chiller heating                         |
| ESC                 | Dual electrode                          |
| Turbo               | 2650L/s                                 |
| Gas Injector        | Symmetric 8 injectors                   |
| Surface Treatement  | Y <sub>2</sub> O <sub>3</sub> Coating   |
| Maintain Time       | 3h                                      |
| SiC Etch Rate       | 6000A/min                               |
| PA                  | > 0.2μm < 30ea                          |
| MTBC                | 200RFH                                  |
| Metal Contamination | Free                                    |
| W×L×H               | 3253×3279×2339 mm                       |

**Principle:**

